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28. (New) An apparatus comprising:

a first single crystal substrate portion having a dielectric layer on a surface, the first substrate portion formed as a film of less than an entire portion of a starting material by demarcating a film thickness through an ion implantation into the starting material and separating the first substrate portion from the starting material; and

a second substrate portion having devices formed thereon and defining a device surface wherein the dielectric layer of the first substrate portion is bonded to the device surface of the second substrate portion.

29. (New) The apparatus of claim 28, further comprising a plurality of devices formed on the first substrate portion.

30. (New) The apparatus of claim 29 wherein selected ones of the devices of the first substrate portion and selected ones of the devices of the second substrate portion are interconnected.

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31. (New) An apparatus comprising:

a primary substrate having a first level of devices formed thereon and defining a device surface;

at least one secondary single crystal substrate coupled to the device surface, the at least one secondary substrate having devices formed thereon.

32. (New) The apparatus of claim 31 wherein selected ones of the first level of devices of the primary substrate and selected ones of the devices of the secondary substrate are interconnected.